



74LX1G14

LOW VOLTAGE CMOS SINGLE SCHMITT INVERTER WITH 5V TOLERANT INPUT

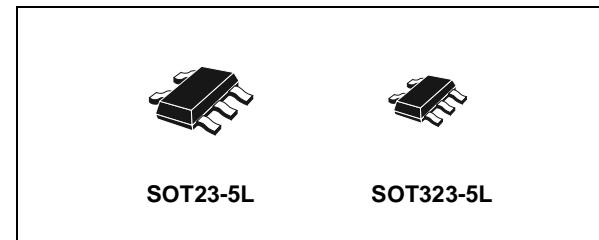
- 5V TOLERANT INPUTS
- HIGH SPEED: $t_{PD} = 7.5\text{ns}$ (MAX.) at $V_{CC} = 3\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- TYPICAL HYSTERESIS: $V_h=1\text{V}$ at $V_{CC}=4.5\text{V}$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OHI}| = I_{OL} = 24\text{mA}$ (MIN) at $V_{CC} = 3\text{V}$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(\text{OPR}) = 1.65\text{V}$ to 5.5V
(1.2V Data Retention)
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74LX1G14 is a low voltage CMOS SINGLE SCHMITT INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

It is ideal for 1.65 to 5.5 V_{CC} operations and low power and low noise applications. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

Power down protection is provided on input and output and 0 to 7V can be accepted on inputs with



ORDER CODES

PACKAGE	T & R
SOT23-5L	74LX1G14STR
SOT323-5L	74LX1G14CTR

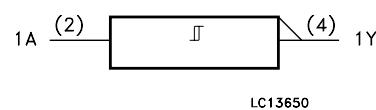
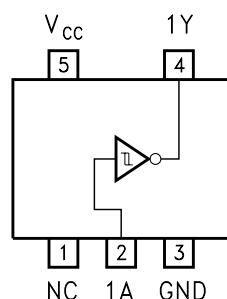
no regard to the supply voltage. It can be interfaced to 5V signal environment for inputs in mixed 3.3/5V system.

Pin configuration and function are the same as those of the 74LX1G04 but the 74LX1G14 has hysteresis.

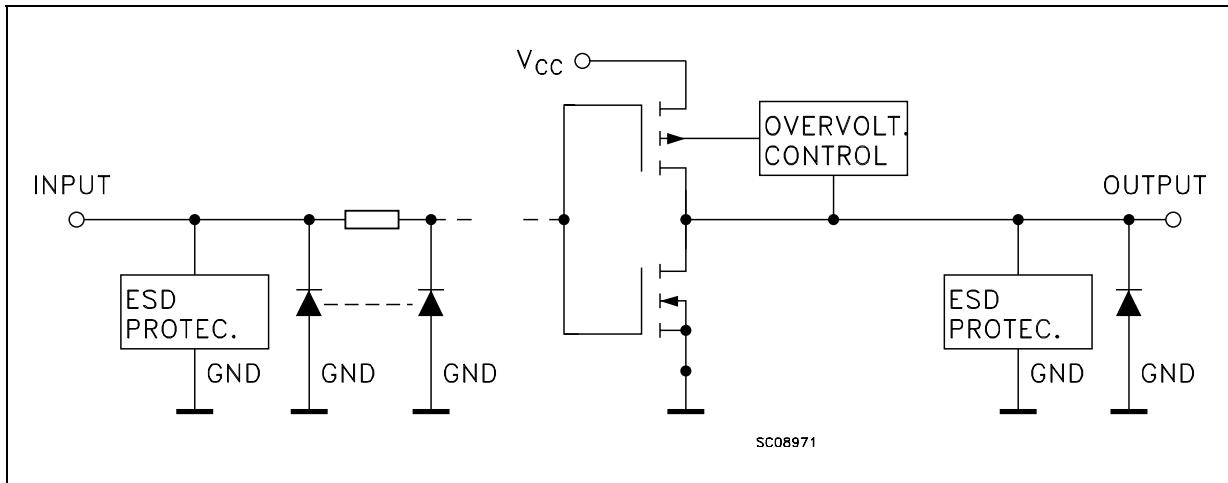
This together with its schmitt trigger function allows it to be used on line receivers with slow rise/fall input signals.

The input is equipped with protection circuits against static discharge, giving it ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1	NC	Not Connected
2	1A	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	H
H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage (V _{CC} = 0V)	-0.5 to +7.0	V
V _O	DC Output Voltage (High or Low State) (note 1)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note 2)	- 50	mA
I _O	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current per Supply Pin	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2V at V_{CC} = 3.0V

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	1.65 to 5.5	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage ($V_{CC} = 0V$)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 4.5$ to 5.5V)	± 32	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to 3.6V)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7$ to 3.0V)	± 12	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.3$ to 2.7V)	± 8	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 1.65$ to 2.3V)	± 4	mA
T_{op}	Operating Temperature	-55 to 125	°C

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2V at $V_{CC} = 3.0V$

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value				Unit	
		V_{CC} (V)		-40 to 85 °C		-55 to 125 °C			
				Min.	Max.	Min.	Max.		
V_{T+}	Positive Input threshold	1.65		0.79	1.16	0.79	1.16	V	
		2.3		1.11	1.56	1.11	1.56		
		3		1.5	1.87	1.5	1.87		
		4.5		2.16	2.74	2.16	2.74		
		5.5		2.61	3.33	2.61	3.33		
V_{T-}	Negative Input threshold	1.65		0.39	0.62	0.39	0.62	V	
		2.3		0.58	0.87	0.58	0.87		
		3		0.84	1.14	0.84	1.14		
		4.5		1.41	1.79	1.41	1.79		
		5.5		1.87	2.29	1.87	2.29		
V_{OH}	High Level Output Voltage	1.65 to 4.5	$I_O = -100 \mu A$	$V_{CC} - 0.1$		$V_{CC} - 0.1$		V	
		1.65	$I_O = -4 mA$	1.2		1.2			
		2.3	$I_O = -8 mA$	1.9		1.9			
		3.0	$I_O = -16 mA$	2.4		2.4			
			$I_O = -24 mA$	2.2		2.2			
		4.5	$I_O = -32 mA$	3.8		3.8			
V_{OL}	Low Level Output Voltage	1.65 to 4.5	$I_O = 100 \mu A$		0.1		0.1	V	
		1.65	$I_O = 4 mA$		0.45		0.45		
		2.3	$I_O = 8 mA$		0.3		0.3		
		3.0	$I_O = 16 mA$		0.4		0.4		
			$I_O = 24 mA$		0.55		0.55		
		4.5	$I_O = 32 mA$		0.55		0.55		
V_H	Hysteresis Voltage	1.65		0.37	0.62	0.37	0.62	V	
		2.3		0.48	0.77	0.48	0.77		
		3		0.56	0.87	0.56	0.87		
		4.5		0.71	1.04	0.71	1.04		
		5.5		0.71	1.11	0.71	1.11		
I_I	Input Leakage Current	1.65 to 5.5	$V_I = 0$ to 5.5V		± 10		± 10	μA	
I_{off}	Power Off Leakage Current	0	V_I or $V_O = 5.5V$		10		10	μA	
I_{CC}	Quiescent Supply Current	1.65 to 5.5	$V_I = V_{CC}$ or GND		10		10	μA	

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition				Value				Unit	
		V_{CC} (V)	C_L (pF)	R_L (Ω)	$t_s = t_r$ (ns)	-40 to 85 °C		-55 to 125 °C			
						Min.	Max.	Min.	Max.		
t_{PLH} t_{PHL}	Propagation Delay Time	1.65 to 1.95	15	1M Ω	3.0	2	15.6	2	15.6	ns	
		2.3 to 2.7				1	9.5	1	9.5		
		3.0 to 3.6				1	6.5	1	6.5		
		4.5 to 5.5				0.5	5.5	0.5	5.5		
		1.65 to 1.95	30	1000	2.0	1.5	10	1.5	10		
		2.3 to 2.7	30	500	2.0	2	5.5	2	5.5		
		2.7	50	500	2.5	1.5	5.5	1.5	5.5		
		3.0 to 3.6	50	500	2.5	1.5	7.5	1.5	7.5		
		4.5 to 5.5	50	500	2.5	0.8	6.2	0.8	6.2		

(*) Voltage range is 3.3V ± 0.3V

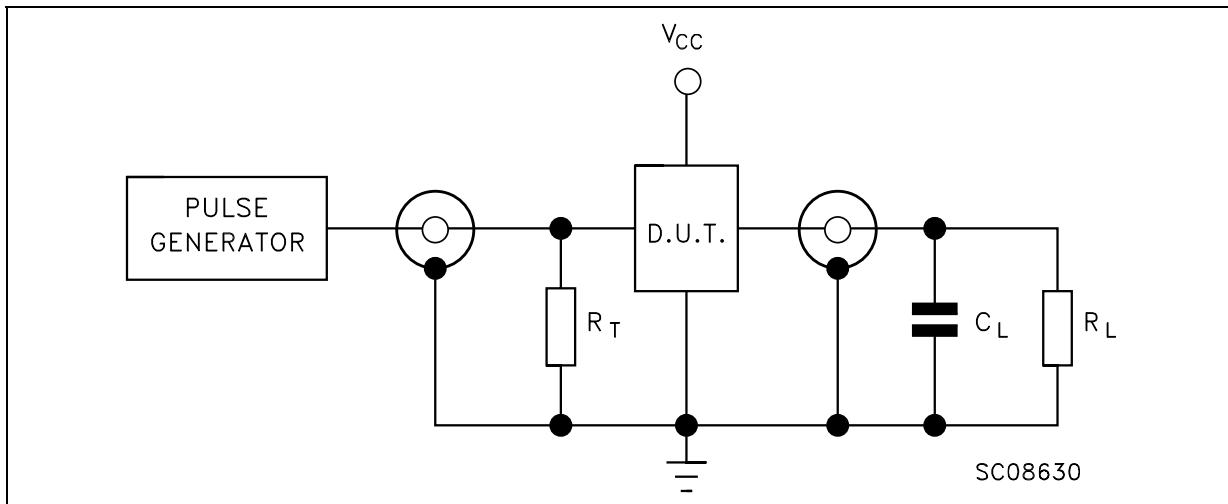
(**) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition				Value			Unit			
		V_{CC} (V)	$T_A = 25$ °C									
			Min.	Typ.	Max.							
C_{IN}	Input Capacitance	0					4			pF		
C_{PD}	Power Dissipation Capacitance (note 1)	1.8	$f_{IN} = 10\text{MHz}$				12			pF		
		2.5					18					
		3.3					24					

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT

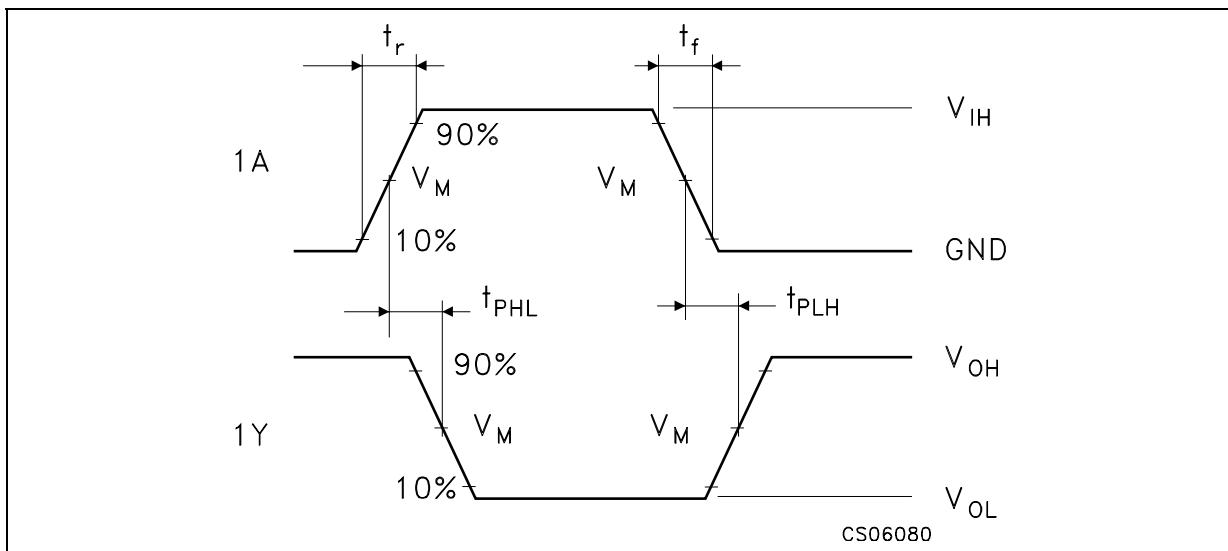


$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

TEST CIRCUIT AND WAVEFORM SYMBOL VALUE

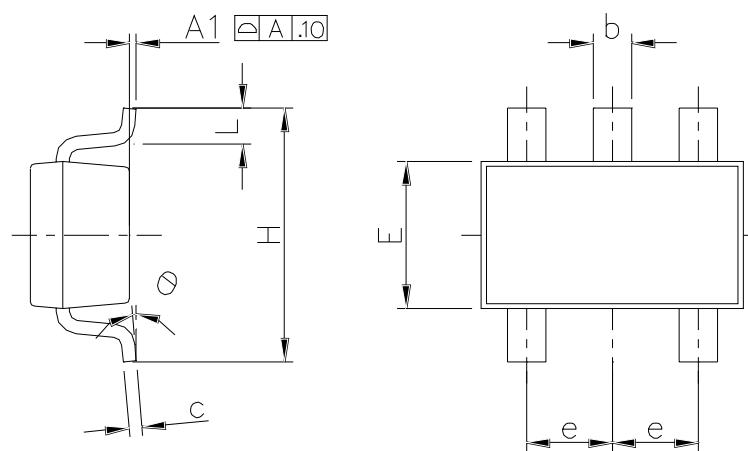
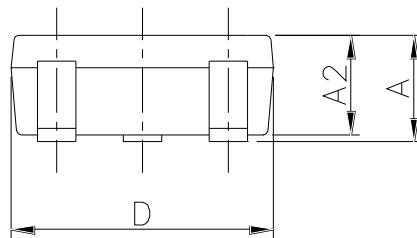
Symbol	V_{CC}		
	1.65 to 1.95V	2.3 to 2.7V	2.7 to 5.5V
C_L	15pF/30pF	15pF/30pF	15pF/50pF
R_L	$1M\Omega/1000\Omega$	$1M\Omega/500\Omega$	$1M\Omega/500\Omega$
V_{IH}	V_{CC}	V_{CC}	V_{CC}
V_M	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$
$t_r = t_f$	<2.0ns	<2.0ns	<2.5ns

WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



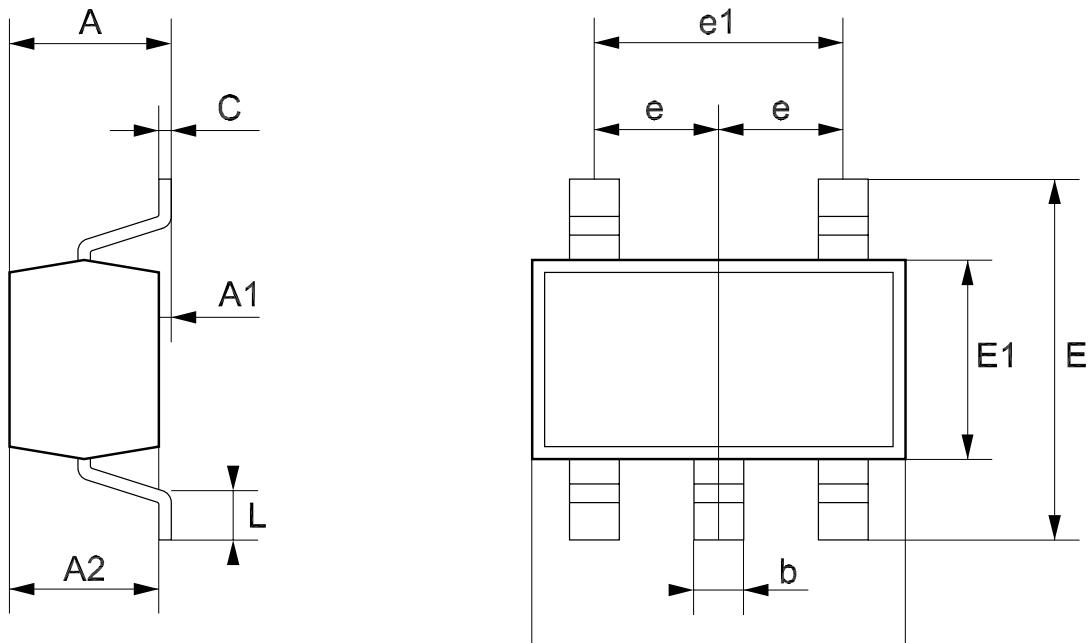
SOT23-5L MECHANICAL DATA						
DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.10	0.0		3.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	1.50		1.75	59.0		68.8
e		0.95			37.4	
H	2.60		3.00	102.3		118.1
L	0.10		0.60	3.9		23.6

DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.10	0.0		3.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	1.50		1.75	59.0		68.8
e		0.95			37.4	
H	2.60		3.00	102.3		118.1
L	0.10		0.60	3.9		23.6



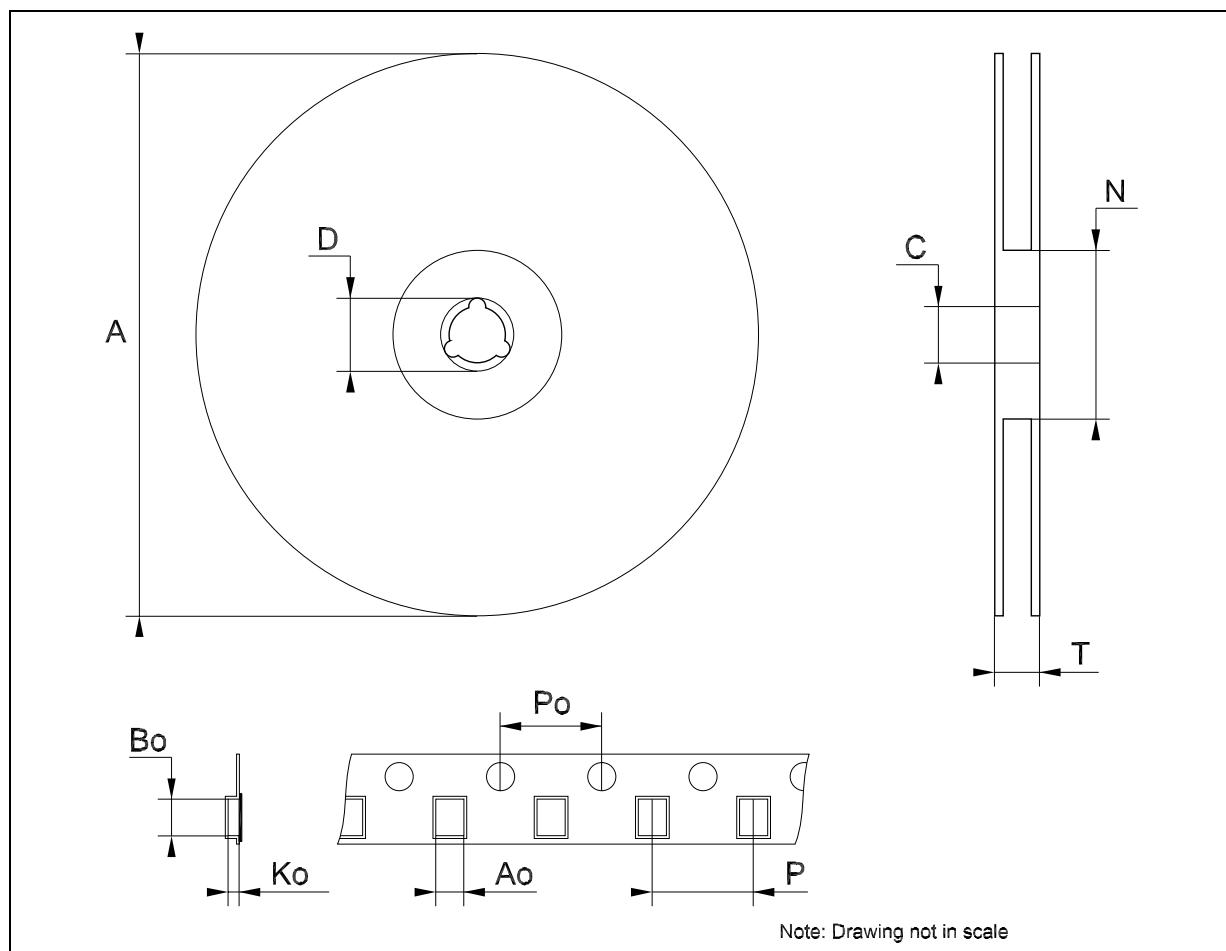
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SOT323-5L MECHANICAL DATA						
DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.80		1.10	31.5		43.3
A1	0.00		0.10	0.0		3.9
A2	0.80		1.00	31.5		39.4
b	0.15		0.30	5.9		11.8
C	0.10		0.18	3.9		7.1
D	1.80		2.20	70.9		86.6
E	1.80		2.40	70.9		94.5
E1	1.15		1.35	45.3		53.1
e		0.65			25.6	
e1		1.3			51.2	
L	0.10		0.30	3.9		11.8

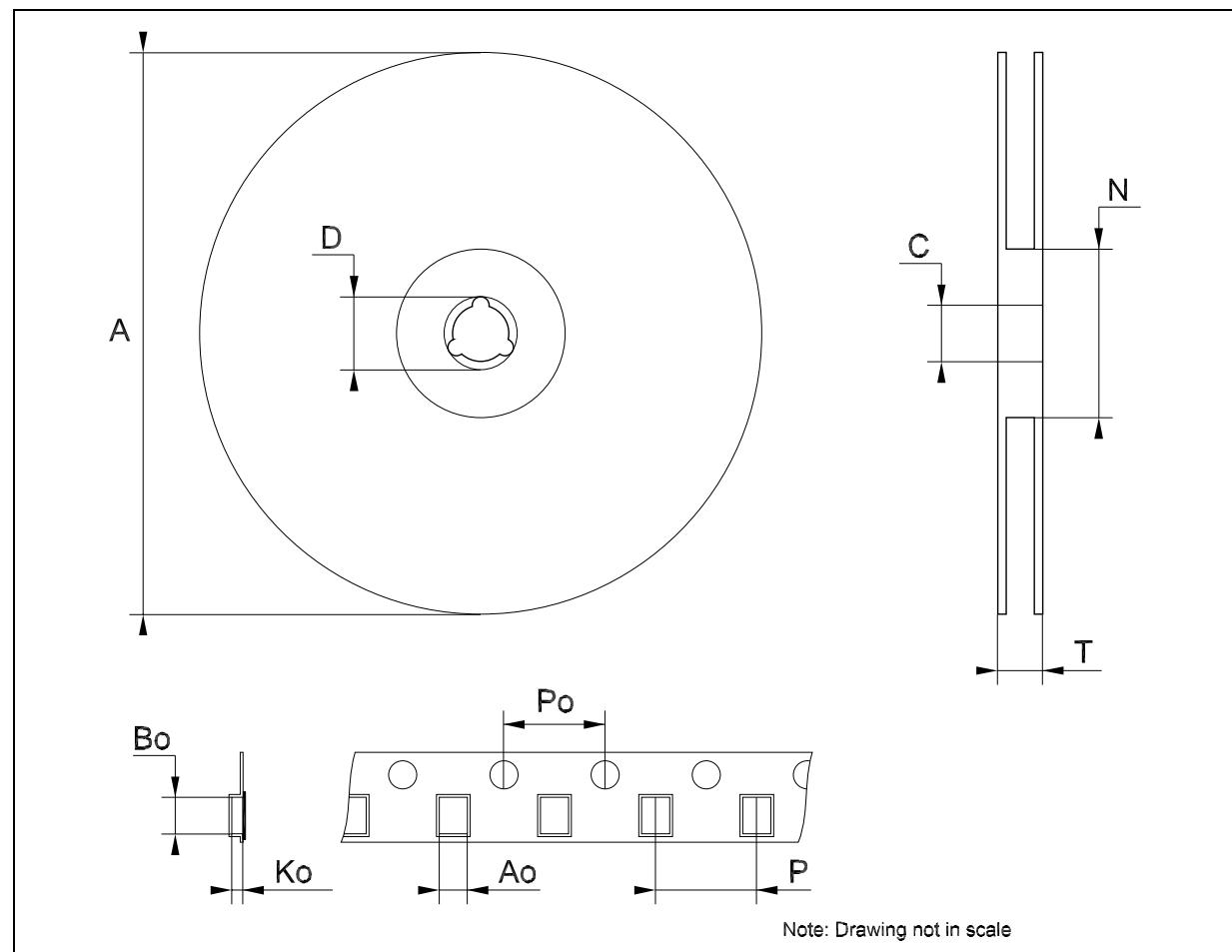


Tape & Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



Tape & Reel SOT323-xL MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	175	180	185	6.889	7.086	7.283
C	12.8	13	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	59.5	60	60.5		2.362	
T			14.4			0.567
Ao		2.25			0.088	
Bo		2.7			0.106	
Ko		1.2			0.047	
Po	3.9	4	4.1	0.153	0.157	0.161
P	3.8	4	4.2	0.149	0.157	0.165



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